

High-Speed Single-Port Synchronous Flex-Repair™ SRAM with Redundancy

Process Technology: TSMC CL013G

sram_4096x8 4096X8, Mux 32, Drive 6

Features

- Precise Optimization for TSMC's Eight-Layer Metal 0.13μm CL013G CMOS Process
- High Density (area is 0.124mm²)
- Fast Access Time (1.56ns at fast@0C process 1.32V, 0°C)
- Fast Cycle Time (1.58ns at fast@0C process 1.32V, 0°C)
- One Read/Write Port
- Completely Static Operation
- Near-Zero Hold Time (Data, Address, and Control Inputs)

Memory Description

The 4096X8 SRAM is a high-performance, synchronous single-port, 4096-word by 8-bit memory designed to take full advantage of TSMC's eight-layer metal, 0.13μm CL013G CMOS process.

The SRAM's storage array is composed of six-transistor cells with fully static memory circuitry. The SRAM operates at a voltage of 1.2V ± 10% and a junction temperature range of -40°C to +125°C.

Pin Description

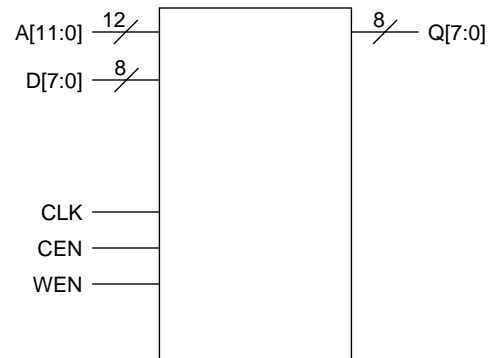
Pin	Description
A[11:0]	Addresses (A[0] = LSB)
D[7:0]	Data Inputs (D[0] = LSB)
CLK	Clock Input
CEN	Chip Enable
WEN	Write Enable
Q[7:0]	Data Outputs (Q[0] = LSB)

Area

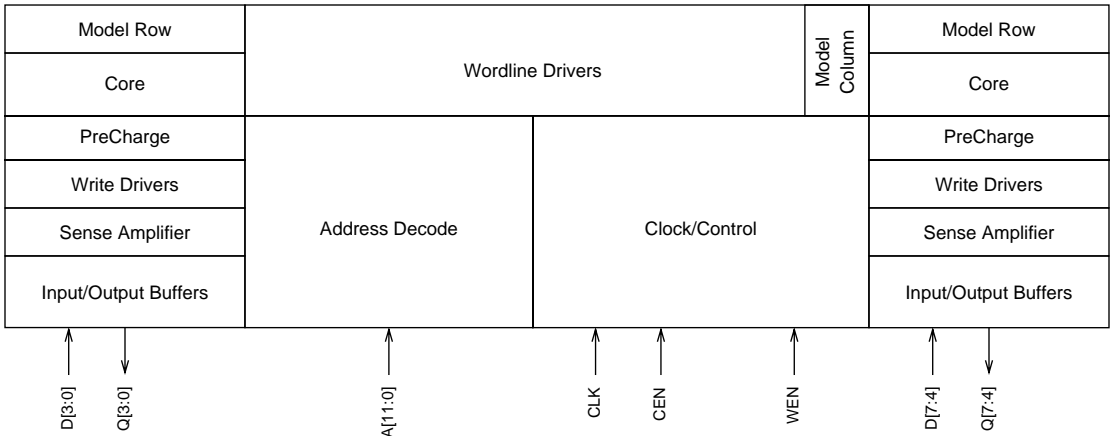
Area Type	Width (mm)	Height (mm)	Area (mm ²)
Core	0.414	0.301	0.124
Footprint	0.424	0.311	0.132

The footprint area includes the core area and user-defined power ring and pin spacing areas.

Symbol

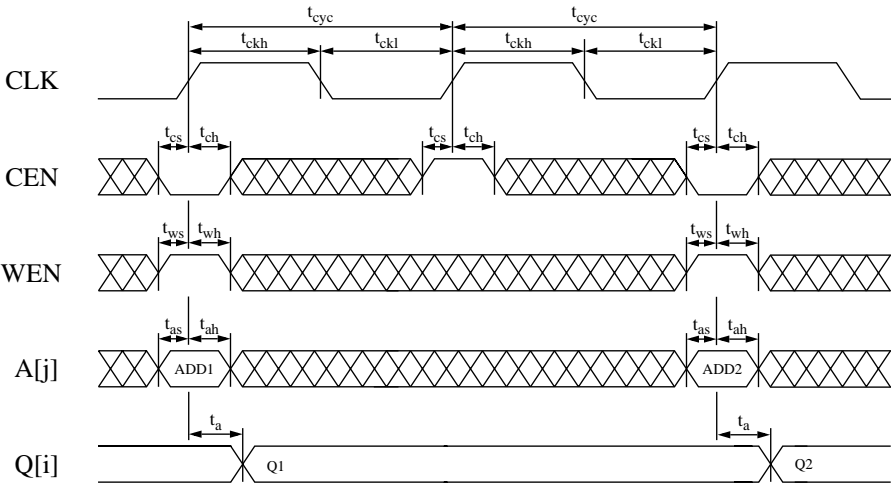


SRAM Block Diagram



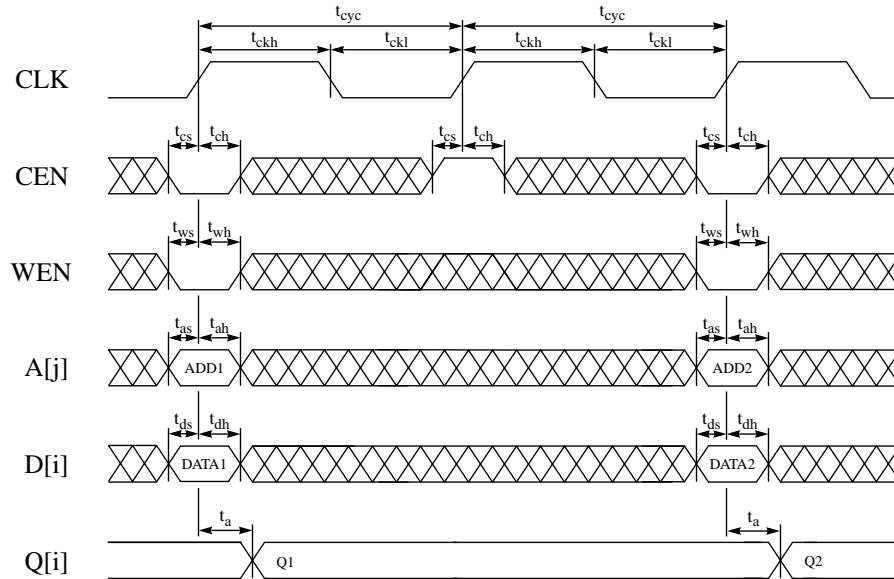
Mission Mode

Figure 1. Synchronous Single-Port SRAM Read-Cycle Timing



Rising delays are measured at 50% of VDD and falling delays are measured at 50% of VDD.
Rising and falling slews are measured from 10% VDD to 90% VDD.

Synchronous Single-Port SRAM Write-Cycle Timing



Rising delays are measured at 50% of VDD and falling delays are measured at 50% of VDD.

Rising and falling slews are measured from 10% VDD to 90% VDD.

SRAM Logic Table

CEN	WEN	Data Out	Mode	Function
H	X	Last Data	Standby	Address inputs are disabled; data stored in the memory is retained, but the memory cannot be accessed for new reads or writes. Data outputs remain stable.
L	L	Data In	Write	Data on the data input bus D[n-1:0] is written to the memory location specified on the address bus A[m-1:0], and driven through to the data output bus Q[n-1:0].
L	H	SRAM Data	Read	Data on the data output bus Q[n-1:0] is read from the memory location specified on the address bus A[m-1:0].

SRAM Timing: Mission Mode

Parameter	Symbol	Fast@-40C Process 1.32V, -40°C		Fast@0C Process 1.32V, 0°C		Typical Process 1.20V, 25°C		Slow Process 1.08V, 125°C	
		Min (ns)	Max (ns)	Min (ns)	Max (ns)	Min (ns)	Max (ns)	Min (ns)	Max (ns)
Cycle time	t_{cyc}	1.02		1.09		1.58		2.63	
Access time ^{1,2}	t_a	0.90			0.97		1.56		2.65
Address setup	t_{as}	0.18		0.19		0.30		0.54	
Address hold	t_{ah}	0.01		0.01		0.01		0.00	

Parameter	Symbol	Fast@-40C Process 1.32V, -40°C		Fast@0C Process 1.32V, 0°C		Typical Process 1.20V, 25°C		Slow Process 1.08V, 125°C	
		Min (ns)	Max (ns)	Min (ns)	Max (ns)	Min (ns)	Max (ns)	Min (ns)	Max (ns)
Chip enable setup	t _{cs}	0.27		0.29		0.40		0.65	
Chip enable hold	t _{ch}	0.00		0.00		0.00		0.00	
Write enable setup	t _{ws}	0.28		0.28		0.39		0.61	
Write enable hold	t _{wh}	0.00		0.00		0.00		0.00	
Data setup	t _{ds}	0.13		0.14		0.22		0.36	
Data hold	t _{dh}	0.00		0.00		0.00		0.00	
Clock high	t _{ckh}	0.04		0.04		0.06		0.10	
Clock low	t _{ckl}	0.11		0.11		0.17		0.29	
Clock rise slew	t _{ckr}		4.00		4.00		4.00		4.00
Output load factor (ns/pF)	K _{load}		0.52		0.54		0.71		1.06

¹ Parameters have a load dependence (K_{load}), which is used to calculate: $TotalDelay = FixedDelay + (Kload \times Cload)$.

² Access time is defined as the slowest possible output transition for the typical and slow corners, and the fastest possible output transition for the fast corner.

Pin Capacitance

Pin	Fast@-40C Process 1.32V, -40°C	Fast@0C Process 1.32V, 0°C	Typical Process 1.20V, 25°C	Slow Process 1.08V, 125°C
	Value (pF)	Value (pF)	Value (pF)	Value (pF)
A[j]	0.019	0.019	0.018	0.017
D[i]	0.002	0.002	0.002	0.001
CLK	0.171	0.176	0.157	0.149
CEN	0.007	0.007	0.007	0.006
WEN	0.007	0.007	0.007	0.007

Power

100.00MHz Operation

Condition	Fast@-40C Process 1.32V, -40°C	Fast@0C Process 1.32V, 0°C	Typical Process 1.20V, 25°C	Slow Process 1.08V, 125°C
	Value (mA)	Value (mA)	Value (mA)	Value (mA)
AC Current ¹	4.757	4.869	4.133	3.627
Read AC Current	4.045	4.163	3.486	2.978
Write AC Current	5.468	5.575	4.781	4.276
Peak Current	300.178	275.371	169.489	101.928
Deselected Current ²	0.641	0.668	0.559	0.520
Standby Current ³	0.004	0.017	0.006	0.034

¹ Value assumes 50% read and write operations, where all addresses and 50% of input and output pins switch.

² Value assumes SRAM is deselected, all addresses switch, and 50% of input pins switch. The logic-switching component of deselected power becomes negligibly small if the input pins are held stable by externally controlling these signals with chip select.

³ Value is independent of frequency and assumes all inputs and outputs are stable.

Clock Noise Limit

Signal	Fast@-40C Process 1.32V, -40°C		Fast@0C Process 1.32V, 0°C		Typical Process 1.20V, 25°C		Slow Process 1.08V, 125°C	
	Pulse Width (ns)	Voltage (V)	Pulse Width (ns)	Voltage (V)	Pulse Width (ns)	Voltage (V)	Pulse Width (ns)	Voltage (V)
CLK	10.00	0.61	10.00	0.59	10.00	0.62	10.00	0.59

The clock noise limit is the maximum CLK voltage allowable for the indicated pulse width without causing a spurious memory cycle or other memory failure.

Power and Ground Noise Limit

Signal	Fast@-40C Process 1.32V, -40°C	Fast@0C Process 1.32V, 0°C	Typical Process 1.20V, 25°C	Slow Process 1.08V, 125°C
	Voltage (V)	Voltage (V)	Voltage (V)	Voltage (V)
Power	0.13	0.13	0.12	0.11
Ground	0.13	0.13	0.12	0.11

The power/ground noise limit is the maximum supply voltage transition allowable without causing a memory failure.